

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
Hans Norström et al.

§ Group Art Unit:
§

Serial No.:

§ Examiner:
§

Filing Date: **April 21, 2004**

§ Attny. Docket No. **068758.0182**
Title: **Silicon-Germanium Mesa Transistor** § Client Ref.: **P14802US1/RF/HS**

Mail Stop Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

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PURSUANT TO 37 C.F.R. § 1.10, I HEREBY CERTIFY THAT I HAVE INFORMATION AND A REASONABLE BASIS FOR BELIEF THAT THIS CORRESPONDENCE WILL BE DEPOSITED WITH THE U.S. POSTAL SERVICE AS EXPRESS MAIL POST OFFICE TO ADDRESSEE, ON THE DATE BELOW, AND IS ADDRESSED TO:

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INFORMATION DISCLOSURE STATEMENT

Sir:

Applicants respectfully request, pursuant to 37 C.F.R. §§1.56, 1.97 and 1.98, that the art listed on the attached PTO-1449 form be considered and cited in the examination of the above-identified application. A copy of the cited art is enclosed for the convenience of the Examiner.

Furthermore, pursuant to 37 C.F.R. §§1.97(g) and (h), no representation is made that these references are material to the patentability of the present application.

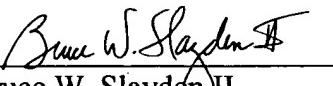
As the Information Disclosure Statement is being submitted before the mailing of the first office action on the merits, Applicants believe that no fee is required. If a fee is

required, please accept this transmittal as a petition therefor and charge any fee to Baker Botts L.L.P. (*formerly, Baker & Botts, L.L.P.*) Deposit Account No. 02-0383, Order No. (068758.0182) for any other charges necessary for the filing of this Information Disclosure Statement.

BAKER BOTTS L.L.P. (023640)

Date: April 21, 2004

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| PTO-1449 Information Disclosure Citation in an Application | | | Application No. Docket Number 068758.0182 | Applicant(s): Hans Norström et al. | | | | |
|---|------------------|---|---|---|----------------|----------|-------------|---|
| | | | Group Art Unit | | Filing Date | | | |
| | | | | | April 21, 2004 | | | |
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| 8 | WO 01/20664 | 03-22-01 | | PCT | H01L | 21/76 | x | |
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| EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant. | | | | | | | | |